EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13066	(fet or (field adj effect adj transistor) or transistor or (circuit or circuitry)) with (defect or defective) with (detect or detecting or detected or detection or sense or sensing or sensed or sensor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:14
L2	9	(fet or (field adj effect adj transistor) or transistor or (circuit or circuitry)) with (defect or defective) with (detect or detecting or detected or detection or sense or sensing or sensed or sensor) and (nanotube or nano-tube or (nano near tube))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:16
L3	44	"6630772" or "6437329" or "20030218224" or "20010023986"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:19
L4	12	l3 and (defect or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:21
L5	6	(((cnt or (carbon near nanotube)) or nanotube) near10 (defect or defective) near5 (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:23
L6	6	(((cnt or (carbon near nanotube)) or nanotube) near10 (defect or defective) near (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:23
L7	2	((((carbon near nanotube)) or nanotube) near10 (defect or defective) near (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:24
L8	2	((((carbon near nanotube)) or nanotube) with (defect or defective) near (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:24

L9	600	(((carbon near nanotube)) or nanotube) with (defect or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:24
L10	12	(((carbon near nanotube)) or nanotube) with (detect or detecting or detected or detecion or sense or sensing or sensed or sensor) with (defect or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:26
L11	124	(((carbon near nanotube)) or nanotube) with (detect or detecting or detected or detecion or sense or sensing or sensed or sensor) with (defect or defective or measure or measuring or measured or measurement)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:26
L12	156	(((carbon near nanotube)) or nanotube) with (detect or detecting or detected or detecion or sense or sensing or sensed or sensor) with (defect or stress or strain or defective or measure or measuring or measured or measurement)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:26
L13	107	(((carbon near nanotube)) or nanotube) near10 (detect or detecting or detected or detecion or sense or sensing or sensed or sensor) with (defect or stress or strain or defective or measure or measuring or measured or measurement)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:27
L14	101	(((carbon near nanotube)) or nanotube) near10 (detect or detecting or detected or detecion or sense or sensing or sensed or sensor) near10 (defect or stress or strain or defective or measure or measuring or measured or measurement)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:27
L15	31	(((carbon near nanotube)) or nanotube) near10 (detect or detecting or detected or detecion or sense or sensing or sensed or sensor or measure or measuring or measured or measurement) near10 (defect or stress or strain or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:41

L16	3	(((carbon near nanotube)) or nanotube) near10 (detect or detecting or detected or detecion or sense or sensing or sensed or sensor or measure or measuring or measured or measurement) near10 (defect or stress or strain or defective) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:42
L17	2	(((carbon near nanotube)) or nanotube) near10 (detect or detecting or detected or detecion or sense or sensing or sensed or sensor or measure or measuring or measured or measurement) near10 (defect or stress or strain or defective) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:42
L18	6	(((carbon near nanotube)) or nanotube) with (detect or detecting or detected or detecion or sense or sensing or sensed or sensor or measure or measuring or measured or measurement) with (defect or stress or strain or defective) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:45
L19	300	(((carbon near nanotube)) or nanotube) near2 (sensor or detector or detecting or detection or sensing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:47
L20	113	(((carbon near nanotube)) or nanotube) near2 (sensor or detector or detecting or detection or sensing) and (defect or defective or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:48
L21	36	(((carbon near nanotube)) or nanotube) near2 (sensor or detector or detecting or detection or sensing) and (defect or defective or stress or strain) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:49
L22	3	((((carbon near nanotube)) or nanotube) near5 transistor) near2 (sensor or detector or detecting or detection or sensing) and (defect or defective or stress or strain) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:49

EAST Search History

L23	4	((((carbon near nanotube)) or nanotube) near5 transistor) near2 (sensor or detector or detecting or detection or sensing or detect) and (defect or defective or stress or strain) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:50
L24	10	((((carbon near nanotube)) or nanotube) near5 transistor) near10 (sensor or detector or detecting or detection or sensing or detect) and (defect or defective or stress or strain) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:50
L25	990	(strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:52
L26	66	((strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:53
L27	4	((strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor) and (((carbon near nanotube) or nanotube) near5 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:55
L28	990	((strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:55

EAST Search History

L29	16	((strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor).clm. and ((strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:58
L30	990	((strain or stress or defect or defective) near10 (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:59
L31	1158	((strain or stress or defect or defective) with (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) near10 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:59
L32	1525	((strain or stress or defect or defective) with (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) with transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 13:59
L33	4	((strain or stress or defect or defective) with (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) with transistor) and (((carbon near nanotube) or nanotube) near10 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:00

EAST Search History

L34	8	((strain or stress or defect or defective) with (measure or measuring or measured or measurement or sense or sensing or sensed or sensor or detect or detecting or detected or detection) with transistor) and (((carbon near nanotube) or nanotube))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:02
L35	224	(transistor with ((defect or defective) near (circuit or circuitry)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:03
L36	160	(transistor near10 ((defect or defective) near (circuit or circuitry)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:03
L37	24	(transistor near10 (detect or detecting or detected) near10 ((defect or defective) near (circuit or circuitry)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:03
L38	7	(transistor near5 (detect or detecting or detected) near5 ((defect or defective) near (circuit or circuitry)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:06
L39	0	(transistor near5 (detect or detecting or detected) near5 ((defect or defective) near (circuit or circuitry))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:06
L40	2	(transistor near10 (detect or detecting or detected) near5 ((defect or defective) near (circuit or circuitry))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:06
L41	3	(transistor near10 (detect or detecting or detected) near10 ((defect or defective) near (circuit or circuitry))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:07
L42	2	(transistor near10 (detect or detecting or detected) near10 ((defect or defective) near (circuit or circuitry))).clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:07

EAST Search History

L43	2	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective) near (circuit or circuitry))).clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:07
L44	2	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or straing) near (circuit or circuitry))).clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:08
L45	2	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain) near (circuit or circuitry))). clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:08
L46	44	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain))).clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:08
L47	38	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain))).clm. and gate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:08
L48	1	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain))).clm. and gate.clm. and nanotube	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:08
L49	1	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain))) and gate.clm. and nanotube	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:08

EAST Search History

L50	4	(transistor near10 (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain))) and gate and nanotube	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:09
L51	4	(transistor with (measure or measuring or measured or measurement or detect or detecting or detected) near10 ((defect or defective or stress or strain))) and gate and nanotube	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:09
L52	5	(transistor with (measure or measuring or measured or measurement or detect or detecting or detected) with ((defect or defective or stress or strain))) and gate and nanotube	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:09
L53	8	(transistor with (measure or measuring or measured or measurement or detect or detecting or detected or sensor or sense or sensing) with ((defect or defective or stress or strain))) and gate and nanotube	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:10
L54	17430	((defect or defective) near2 (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:10
L55	9	transistor near2 (detect or detecting or detected or detection) near2 ((defect or defective) near2 (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:11
L56	44	transistor near5 (detect or detecting or detected or detection) near2 ((defect or defective) near5 (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:12
L57	5	transistor near5 (detect or detecting or detected or detection) near2 ((defect or defective) near (circuit or circuitry))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:35

EAST Search History

L58	108	(US-20050129573-$ or US-20050249249-$ or US-20060006377-$ or US-20050218397-$ or US-20040253741-$ or US-20050218398-$ or US-20050133372-$ or US-20040022943-$ or US-20040224490-$ or US-20060024871-$ or US-20030068432-$ or US-20060038179-$ or US-20050012163-$ or US-20040240252-$ or US-20060065887-$ or US-20050110064-$ or US-20030089899-$ or US-20040016928-$ or US-20050230822-$ or US-20050181587-$ or US-20030170930-$ or US-20050247929-$ or US-20020179434-$ or US-20050079659-$ or US-20030122133-$ or US-20040173378-$).did. or (US-20040079892-$ or US-20030218224-$ or US-20020030646-$ or US-20050059210-$ or US-20040101685-$ or US-20040214786-$ or US-20060052947-$ or US-20050231855-$ or US-20010023986-$ or US-20030178617-$ or US-20060054922-$ or US-20050161668-$ or US-20050056826-$ or US-20060038167-$ or US-20050212014-$ or US-20060135374-$ or US-20040012062-$).did. or (US-6921462-$ or US-6988925-$ or US-6902457-$ or US-6958572-$ or US-6979947-$ or US-6730972-$ or US-6645028-$ or US-6919592-$ or US-6769945-$ or US-6787122-$ or US-6437329-$ or US-6043689-$ or US-6911682-$ or US-6891227-$ or US-6784028-$ or US-6998103-$ or US-6841002-$ or US-6465813-$ or US-6630772-$ or US-6848320-$ or US-7008563-$ or US-6841003-$ or US-7026432-$ or US-6975063-$ or US-6948995-$ or US-6836424-$).did. or (US-6920680-$ or US-6643165-$	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/12 14:37

EAST Search History

L59	2	l58 and cntfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:38
L60	43	l58 and (cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:40
L61	29	l58 and (cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor)) and gate and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:42
L62	19	l58 and (cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor)) and gate and source and drain and (detect or detecting or detected or detection or sensor or sense or sensing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:43
L63	17	l58 and (cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor)) and gate and source and drain and (detect or detecting or detected or detection or sensor or sense or sensing) and (defect or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:43
L64	17	l58 and (cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor)) and gate and source and drain and (detect or detecting or detected or detection or sensor or sense or sensing) and (defect or defective or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:43
L65	3	(cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor)).clm. and gate and source and drain and (detect or detecting or detected or detection or sensor or sense or sensing) and (defect or defective or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:44

EAST Search History

L66	38	(cntfet or (carbon near nanotube near FET) or (carbon near nanotube near field near effect near transistor)) and gate and source and drain and (detect or detecting or detected or detection or sensor or sense or sensing) and (defect or defective or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/12 14:44